

L Number	Hits	Search Text	DB	Time stamp
4	146721	((silicon near oxide) (SiO."sub.2")) and ((silicon near nitride) SiN)) ONO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/28 13:48
5	75879	pillar	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/28 13:49
6	193595	source and drain and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/28 13:49
7	1026608	(sidewall\$1 (side near wall\$1) spacer\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/28 13:49
8	595	((((silicon near oxide) (SiO."sub.2")) and ((silicon near nitride) SiN)) ONO) and pillar and (source and drain and gate) and ((sidewall\$1 (side near wall\$1) spacer\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/28 13:50

L Number	Hits	Search Text	DB	Time stamp
1	576	charge near trap\$4 near (layer film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/28 16:30
2	1463277	memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/28 16:30
3	462	(charge near trap\$4 near (layer film)) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/28 16:30